2STC5200

High power NPN epitaxial planar bipolar transistor

Features

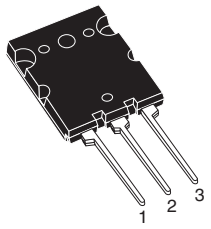
- High breakdown voltage V_{CEO} > 230V
- Complementary to 2STA1943
- Fast-switching speed
- Typical f_T = 30 MHz

Application

- Audio power amplifier

Description

This device is a NPN transistor manufactured using new BiT-LA (Bipolar Transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.



TO-264

Figure 1. Internal schematic diagram

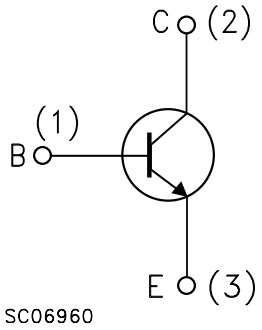


Table 1. Device summary

Order code	Marking	Package	Packaging
2STC5200	2STC5200	TO-264	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage (I_E = 0)	230	V
V_{CEO}	Collector-emitter voltage (I_B = 0)	230	V
V_{EBO}	Emitter-base voltage (I_C = 0)	5	V
I_C	Collector current	15	A
I_{CM}	Collector peak current	30	A
P_{tot}	Total dissipation at T_C = 25°C	150	W
T_{stg}	Storage temperature	-55 to 150	°C
T_J	Operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJ\text{-}case}$	Thermal resistance junction-case Max	0.83	°C/W

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current (I_E = 0)	V_{CB} = 230 V			5	µA
I_{EBO}	Emitter cut-off current (I_C = 0)	V_{EB} = 5 V			5	µA
$V_{(BR)CEO}$(1)	Collector-emitter breakdown voltage (I_B = 0)	I_C = 50 mA	230			V
$V_{(BR)CBO}$	Collector-base breakdown voltage (I_E = 0)	I_C = 100 µA	230			V
$V_{(BR)EBO}$(1)	Emitter-base breakdown voltage (I_C = 0)	I_E = 1 mA	5			V
$V_{CE(sat)}$(1)	Collector-emitter saturation voltage	I_C = 8 A I_B = 800 mA			3	V
V_{BE}	Base-emitter voltage	I_C = 7 A V_{CE} = 5 V			1.5	V
h_{FE}	DC current gain	I_C = 1 A V_{CE} = 5 V I_C = 7 A V_{CE} = 5 V	80 35		160	
t_{on} t_s t_f	Resistive load Turn-on time Storage time Fall time	V_{CC} = 60 V I_C = 5A I_{B1}= -I_{B2} = 0.5 A		0.24 4.7 0.6		µs µs µs
f_T	Transition frequency	I_C = 1 A V_{CE} = 5 V		30		MHz
C_{CBO}	Collector-base capacitance (I_E = 0)	V_{CB} = 10 V f = 1 MHz		150		pF

1. Pulsed: pulse duration = 300 µs, duty cycle ≤ 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

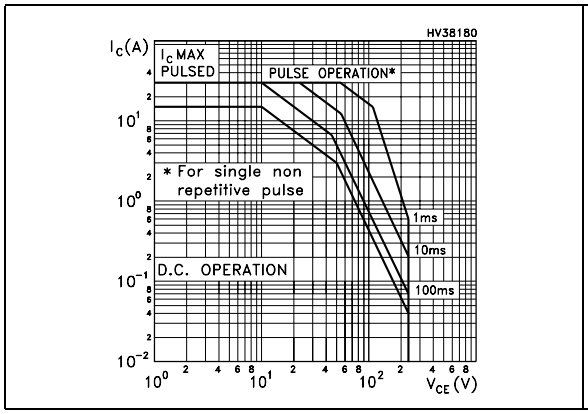


Figure 3. Derating curve

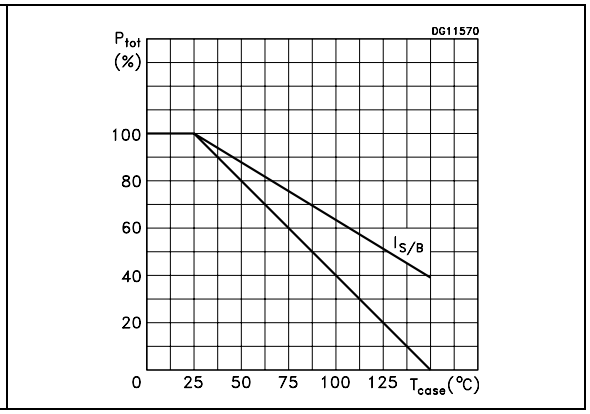


Figure 4. Output characteristics

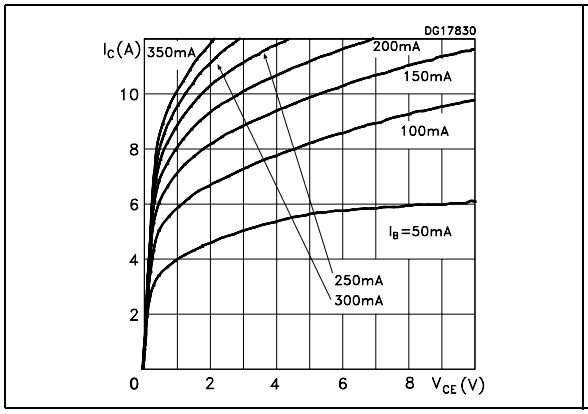


Figure 5. DC current gain

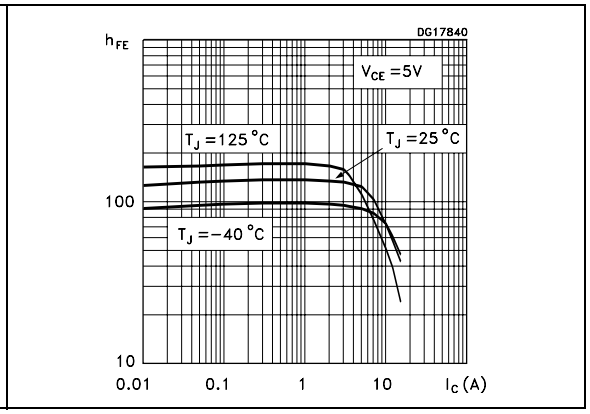


Figure 6. Collector-emitter saturation voltage

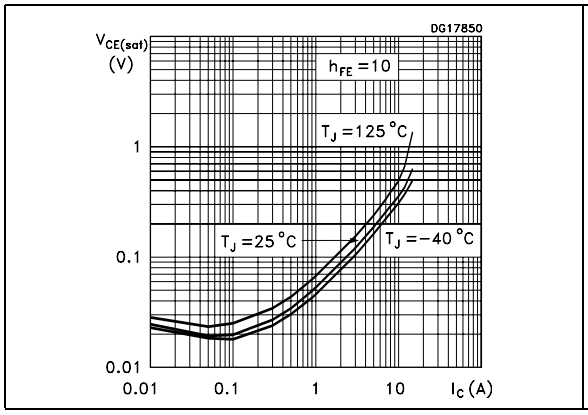
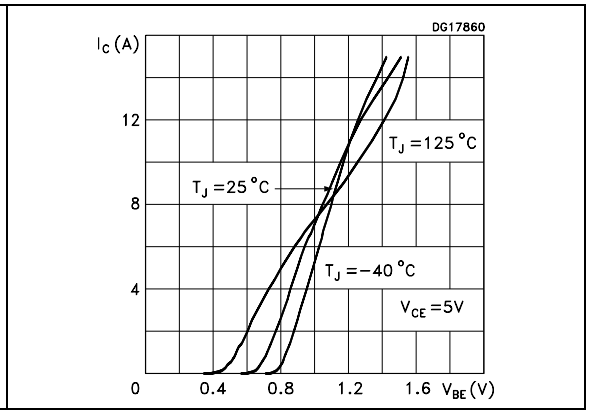
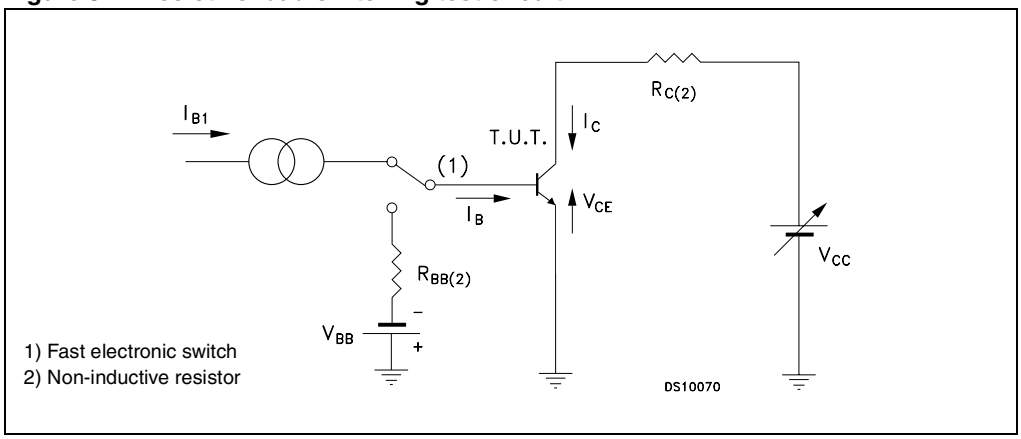


Figure 7. Collector current vs base-emitter voltage



2.2 Test circuit

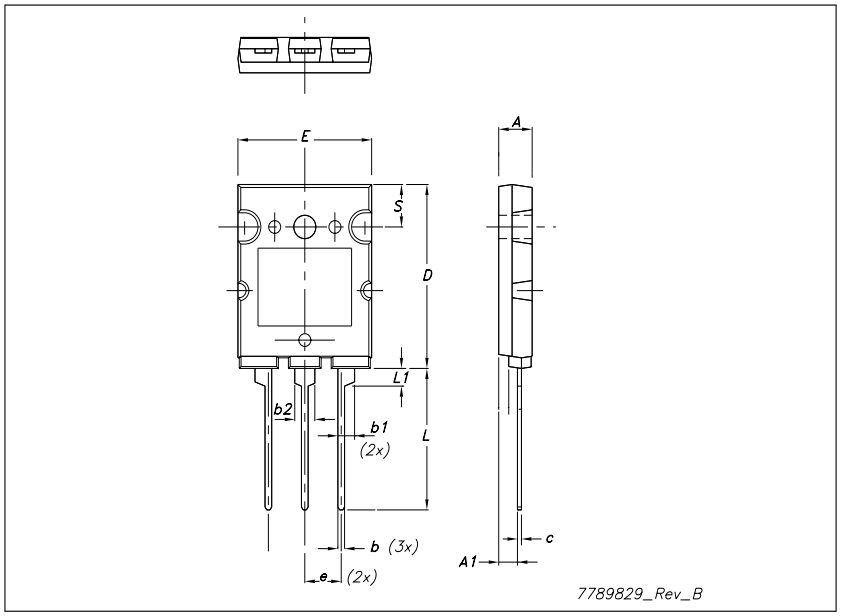
Figure 8. Resistive load switching test circuit



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

TO-264 Mechanical data			
Dim.	**mm.**		
	Min.	**Typ**	**Max.**
A	4.80		5.20
A1	2.50		3.10
b	0.90	1.0	1.25
b1		2.5	
b2		2.8	
c	0.50	0.60	0.85
D	25.6		26.4
E	19.80		20.20
e	5.15		5.75
L	19.50		20.50
L1	2.30		2.70
øP	3.55		3.65



4 Revision history

Table 5. Document revision history

Date	Revision	Changes
19-Jun-2007	1	Initial release.
11-Dec-2007	2	Document promoted from preliminary data to datasheet.